Low Temperature Performance of GaAs MESFETs at L-Band

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A considerable amount of work has been reported on the use of GaAs MESFET amplifiers at cryogenic temperatures. Most of the applications were for frequencies above 4 GHz. In this paper we discuss a 1.4-GHz GaAs MESFET amplifier cooled to 77 K with a noise temperature of less than 20 Kelvins over a 100-MHz bandwidth. The amplifier serves as an IF amplifier for a millimeter-wave cooled mixer.

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